# TFE4152 Design of Integrated Circuits Digital Camera

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# 1 Introduction

"Hello Dirty talk"

# 2 Theory

# 2.1 Analog circuit

The analog circuit has input signals delivered by the digital circuitry, and delivers its output to two ADCs. The analog circuit diagram is given in figure 1, where each of the four pixel block has the circuit given in figure 2.

In detail, the analog circuit consists of 4 pixels in a 2x2 array. Each pixel in the same row shares the same NRE (Not-REad) input which means they are sending data to the ADC at the same time. Each pixel in the same column share the same active load and readout wire, which means they need to send data to the ADC at different times.

## 2.1.1 Conceptual operation of pixel circuit

Schematics for the pixel circuit is given in figure 2. It consists of a photo diode PD1, three switch transistors M1, M2 and M4, one buffer transistor M3 and a charge storage capacitor  $C_S$ . The photo diode is modeled by a diode and an ideal current source in parallel. The current source outputs a current  $I_D$  that is proportional to the illumination intensity on that particular pixel. This current is used to charge the transistor  $C_S$ . Ideally, we want that all of  $I_D$  flows through M1 and into  $C_S$  when EXPOSE is HIGH and all of  $I_D$  flows back through the diode in the photo diode model when EXPOSE is LOW. In that way the voltage on node N2 when EXPOSE has been HIGH for a time t is given by

$$V_{CS}(t) = \frac{1}{C_S} \int_0^t I_D(t)dt. \tag{1}$$

This means the voltage  $V_{CS}$  is proportional to the total illumination on the pixel throughout the exposure time, which is exactly what we want.

But since the camera is supposed to be reusable, we need a way to erase that charge before taking a new picture. That is what M2 is for. Ideally we want M2 to be a perfect switch, so that when ERASE is HIGH,  $C_S$  is instantly uncharged through M2 and when ERASE is LOW, M2 does not conduct any current at all.

For the readout we do not want to connect N2 directly to OUT, since the output wire might be very long and have a big capacitance. Instead, the voltage  $V_{CS}$  controls the conductance through a transistor M3. The higher  $V_{CS}$ , the lower conductance through M3 and higher

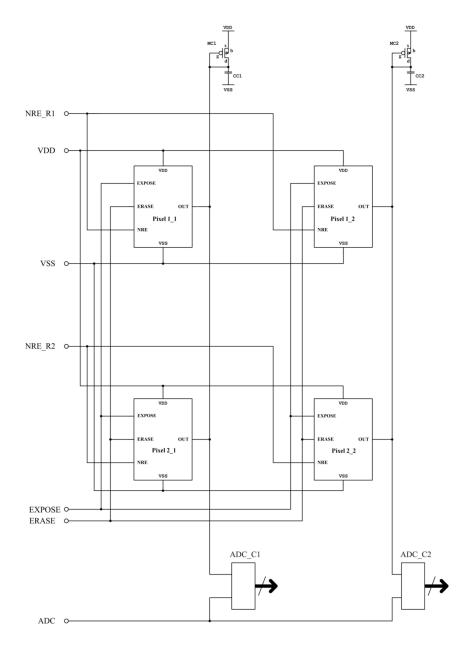


Figure 1: Analog circuit schematic.



Figure 2: Pixel cicuit schematic.

voltage on OUT. In that way, the current required to control the voltage on the output wire is supplied through the active load in the top of each output wire, outside the pixel circit.

But since all pixels in the same column share the same output wire we need a way to unconnect N3 from OUT, and that is what M4 is for. M4 is supposed to be an ideal switch so that the pixel is driving OUT only when NRE is LOW.

#### 2.1.2 Dimensions for switch transistors

The transistors M1, M2 and M4 all function as switches, where a digital gate input decides whether the transistor should act as a short-circuit between drain and source, or as an open circuit. Since these transistors simply should have two possible states, it is key that the leakage current is minimized. This is particularly important for M1 and M2 to ensure that the voltage over  $C_s$  is as constant as possible during readout. In Analog Circuit Design by Tony Chan Carusone, one can read in section 1.4.1 that the subthreshold leakage current is given by

$$I_{off} = (n-1)\mu_n C_{ox} \left(\frac{W}{L}\right) \left(\frac{kT}{q}\right)^2 \exp\left(-qV_t/nkT\right). \tag{2}$$

In order to minimize this leakage current,  $\frac{W}{L}$  need to be as small as possible, meaning the smallest possible width W and the largest possible length L is desired. The technology used will limit the possible width and length of the transistor, thus W and L can be chosen accordingly.

# 2.1.3 Value for $C_s$

To choose a suitable value for  $C_s$  spice simulations can be used. To know what values are the best we will look at the four corner cases for exposure time and light conditions. The corner cases will be denoted exposure-light, so for example max-min is maximum exposure time and minimum light. The voltage over  $C_s$  after exposure in each corner will get different values for different values of  $C_s$ . There are many possible approaches to how these corners should be tuned, and the one that we will apply is the following:

- Max-max corner should make  $C_s$  fully charged.
- Min-min corner should leave  $C_s$  uncharged.
- Min-max and max-min corners should make  $C_s$  half full charged.

The reason for why we want the corners to be like that is beyond the scope of this report.

#### 2.1.4 Values for M3 and active load

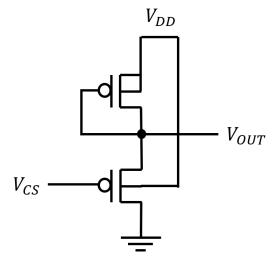


Figure 3: Simplified schematic for output voltage driving circuit.

Values for M3 and active load should be tuned for maximum dynamic range, but it will not have a very big impact since it is a very robust and self-regulating system. If we assume  $C_{C1}$  and  $C_{C2}$  are very small, the output system can be simplified to figure 3. Essentially, the output voltage  $V_{OUT}$  depends on how the conductance in the uppermost and downmost transistor are relative to each other. These conductances are proportional to W/L in the transistors and they also vary with the gate-source voltages. To avoid unnecessary simplifications, it is best to decide these W/L-ratios from SPICE-simulations. The dynamic range

is the difference between the output voltage when uncharged and fully charged, and it is preferable that it is as big as possible.

#### 2.1.5 Process variations

It is important to look at how process variations will impact an analog design. One way to do this is to look at the what is called FF, FS, SF and SS corners. F means fast, S means slow, the first letter is for NMOS and the second is for PMOS. For this design it is enough to look at how the switch transistors are affect by process variations. The values to measure in each corner is  $R_{DS}$  when switched off and on.

For curiosity we will also have a look at how these two corners affect the analog circuit as a whole.

# 2.2 Digital camera controller

The digital input signals in the analog circuit need to be controlled by a digital circuit - the digital camera controller. The module interface for the digital camera controller is described in the figure below.

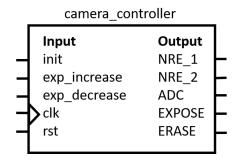


Figure 4: Overview of input and output pins for the camera controller module.

It has inputs *init*,  $exp\_increase$ ,  $exp\_decrease$ , clk and rst. clk is controlled by an internal camera module, while the four other signals are controlled by the user. init is HIGH when the user presses the shutter button,  $exp\_increase$  is HIGH when the user wants to increase the exposure time,  $exp\_decrease$  is HIGH when the user wants to decrease the exposure time (and is overridden by  $exp\_increase$  if they conflict, i.e. if they are HIGH at the same time), and rst is HIGH when the user wishes to cancel any ongoing process, or reset the exposure time

The outputs are NRE\_1, NRE\_2, ADC, EXPOSE and ERASE, all of which were described in section 2.1.

#### 2.2.1 Finite state machine

The wanted behaviour of the digital camera controller is described in the finite state machine (FSM) in figure 5.

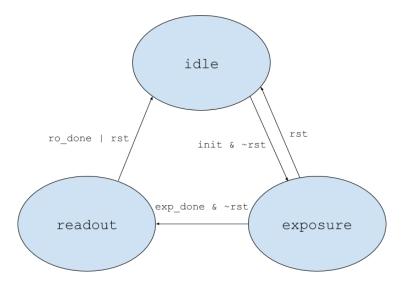


Figure 5: The finite state machine for the digital camera controller.

In the FSM, there are three states. The camera starts in the *idle* state. In this state, the camera isn't in the process of taking any picture, so output signals *EXPOSE* and *ADC* should be LOW, and *NRE\_1* and *NRE\_2* should be HIGH. The camera should also prepare itself for a new picture in this state, so *ERASE* should be HIGH to erase any voltage from the potential previous exposure. The user should be able to adjust the exposure time with the signals *exp\_increase* and *exp\_decrease* in the *idle* state. These signals will respectively increase or decrease the exposure time with 1ms for each clock cycle they're HIGH to a minimum of 2ms and a maximum of 30ms. When the signal *init* is HIGH, the camera will enter the *exposure* state. The exception is if the *rst* input signal is HIGH. In any state, *rst* being HIGH should override any process and take the camera back to *idle*.

When the camera is entering the *exposure* state, *ERASE* should be set LOW and *EXPOSE* should be set HIGH to begin the exposure. If *rst* is HIGH at any time during *exposure*, the camera should return to the *idle* state. When the preset exposure time has passed, the camera should enter the *readout* state if *rst* is LOW. Exposure being finished is called *exp\_done* in figure 5.

The readout state is the final state, in which the data from the individual pixels are read and inputted in the ADC. First, EXPOSE should be set LOW since the exposure is done. Then,  $NRE_{-1}$  should be LOW first at the same time as ADC is HIGH, to read from the top two pixels and input it to the ADC. Lastly,  $NRE_{-2}$  should be LOW at the same time as ADC is HIGH to do the same for the bottom two pixels. Exactly how the output signals should be will be properly explored in the next section. When the readout sequence is finished, called

ro\_done in figure 5, the camera should enter the *idle* state again. As with the *exposure* state, rst being HIGH at any time should return the camera to *idle*. It is important that the camera stays in *idle* for at least one clock cycle before the user is able to take another picture, to ensure that the data of the previous photo is erased.

# 2.2.2 Output timing

The desired time chart is illustrated in figure 6.

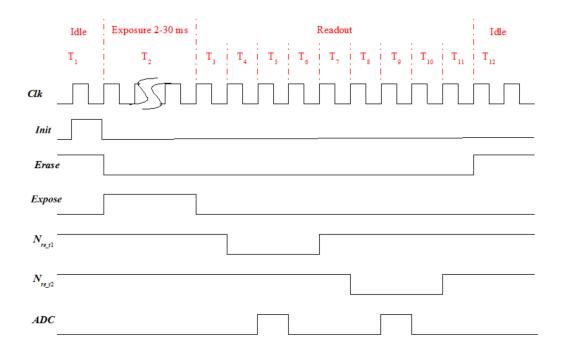


Figure 6: The desired time chart for the output signals of the digital camera controller.

In the *idle* state and *exposure* state, the output signals are as described in the previous subsection. Notably, ERASE is HIGH during *idle* and EXPOSE is HIGH during *exposure*. The *readout* state is more complex, as output signals are altered in every clock cycle. In the first cycle,  $T_3$  in the figure, EXPOSE is set LOW to end exposure before readout begins. From  $T_4$  to  $T_6$ ,  $NRE_1$  is set LOW, with ADC being HIGH in the middle  $T_5$ . This is to ensure that  $NRE_1$  is not transienting from HIGH to LOW or LOW to HIGH while the ADC is reading. In  $T_7$ ,  $NRE_1$  is set HIGH again. From  $T_8$  to  $T_{10}$ , the reading process repeats for  $NRE_2$  to read the bottom two pixels. In the last clock cycle of the state,  $T_{11}$ ,  $NRE_2$  is set HIGH again to end the readout. It can be noted that the *readout* state has a fixed duration of 9 clock cycles, as the only state with a fixed duration.

Table 1: Chosen comp	onent values base	ed on simulations. N	I/A means not	applicable.

Component	W	L	C
M1	$1.08 \mu \mathrm{m}$	$1.08 \mu \mathrm{m}$	N/A
M2	$1.08 \mu \mathrm{m}$	$1.08 \mu \mathrm{m}$	N/A
M3	$5.04 \mu \mathrm{m}$	$0.36 \mu \mathrm{m}$	N/A
M4	$1.08 \mu \mathrm{m}$	$1.08 \mu\mathrm{m}$	N/A
MC1	$1.08 \mu \mathrm{m}$	$1.08 \mu \mathrm{m}$	N/A
MC2	$1.08 \mu \mathrm{m}$	$1.08 \mu \mathrm{m}$	N/A
$C_S$	N/A	N/A	2pF

# 3 Results

# 3.1 Analog pixel circuit

#### 3.1.1 Values and dimensions

The transistor technology used limits the width to

$$1.08\mu \text{m} \le W \le 5.04\mu \text{m}$$
 (3)

and limits the length to

$$0.36\mu \text{m} \le L \le 1.08\mu \text{m}.$$
 (4)

As explained in section 2.1.2, W/L should be as small as possible to reduce leakage current. Therefore the length and width of the switch transistors will be  $1.08\mu m$ .

CS was tuned to 2pF. The output from simulations with this value for the exposure-light corners min-min, min-max, max-min and max-max are shown respectively in figures 9, 10, 11 and 12 in appendix A. These simulations were done by transient analysis of the voltage over  $C_S$  while applying photodiode current and exposure time for the corner cases. The resulting voltage over  $C_S$  is the value at the end of the exposure time.

For M3 and the active load the dynamic range was largest when W/L for M3 was as large as possible and W/L for MC1 and MC2 as small as possible. The simulation used for this is as follows: Simulate a transient analysis on the netlist for the full analog circuit, set  $NRE_{-1}$  LOW and  $NRE_{-2}$  HIGH. ERASE should first be HIGH a little while, then when it gets LOW, EXPOSE goes HIGH, and it should be HIGH long enough for the voltage on the OUT wires to reach its maximum value. The dynamic range is then the difference between the maximum and minimum of this curve. The graph from this simulation with final value is shown in figure 13 in appendix A.

Table 2:  $R_{DS}$  for an NMOS switch in the fast, typical and slow corners.

Corner	Off	On
FF	$5G\Omega$	$500 \mathrm{k}\Omega$
TT	$500G\Omega$	$750 \mathrm{k}\Omega$
SS	$50T\Omega$	$1 \mathrm{M}\Omega$

# 3.1.2 Analog circuit simulation

The simulation of the full analog circuit is shown in figure 17. In this simulation the exposure time was 5ms and the pixels 11, 12, 21 and 22 were exposed by photodiode currents of 750pA, 50pA, 300pA and 100pA respectively.

# 3.1.3 Process variation simulations

The simulation results for  $R_{DS}$  as a function of  $V_{GS}$  for a single NMOS are shown in figures 14, 15 and 16 for FF, TT and SS corners respectively. Table 2 shows what  $R_{DS}$  values this gives when switched fully on and off.

Results from full analog circuit simulation in FF and SS corners are shown in figures 18 and 19 respectively.

# 3.2 Digital circuit

The Verilog code for the digital camera controller is included in appendix 4.2, and the module interface is shown in figure 7.

# camera\_controller

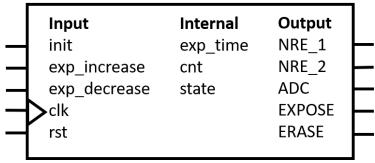


Figure 7: Overview of input and output pins as well as internal registers for the camera controller module.

exp\_time is a 5-bit internal register that holds the exposure time in milliseconds. The

exposure time is 16ms by default, which is the middle value between the minimum 2ms and the maximum 30ms.  $exp\_time$  is only adjusted if  $exp\_increase$ ,  $exp\_decrease$  or rst is HIGH. This means that after a picture is taken, the exposure time is not reset, allowing the user to take multiple pictures in the same lighting without having to tune the exposure time back after each picture. If the user presses the reset button in any of the three states,  $exp\_time$  will return to its default value of 16.

cnt is, like  $exp\_time$ , an internal, 5-bit register. When the camera state switches to exposure or readout, cnt is set to the duration of the state in clock cycles minus one. For every clock cycle in the state thereafter, cnt will decrement. After cnt has reached 0, the state will switch to the next one. The clock frequency is specified as 1kHz in this camera, meaning that one clock cycle lasts for 1ms. The state's duration in clock cycles thus equals its duration in milliseconds. This means that cnt will be set to  $exp\_time - 1$  when the state switches to  $exp\_sure$ , and 8 when the state switches to readout.

state is a 2-bit internal register that holds the state the camera will be in the next clock cycle, respresented by an integer. 0 represents the *idle* state, 1 respresents *exposure*, and 2 represents *readout*. It is important to note that whenever *state* is set to 0, *ERASE* is set to HIGH at the same time, i.e. at the rising edge of the same clock cycle. The camera will therefore not operate as being in the *idle* state and allowing a new picture to be taken before the next rising edge of the clock. This ensures that *ERASE* always is HIGH for at least one clock cycle after a picture is taken or cancelled underway, as described in section 2.2.1.

### 3.2.1 Digital circuit simulation

A showcase of the properties of the implemented camera controller is shown in figure 8. The first five signals in the list to the left are the input signals, the following five are the output signals, and the last three are the internal registers.

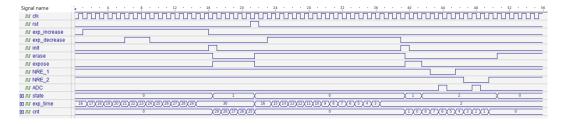


Figure 8: A waveform for the digital camera controller showcasing its properties.

Up until the 16th clock cycle in figure 8, the camera is in the *idle* state. All output signals are true to the *idle* state as it is described in section 2.2.1; *ERASE*, *NRE\_1* and *NRE\_2* are HIGH, and *EXPOSE* and *ADC* are LOW. From the second clock cycle to the 16th, *exp\_increase* is HIGH. *exp\_time* increments for each clock cycle in this interval, until it reaches 30 at the 15th cycle and stays constant. This shows that the exposure time will not exceed 30ms, as specified in section 2.2.1. It has also been made a point from clock cycle seven to nine that

exp\_increase overrides exp\_decrease where they collide, a behaviour which also was specified as intended in section 2.2.1.

In the 17th clock cycle, *init* is HIGH, which sends the camera into the *exposure* state. The output signals act accordingly as *ERASE* goes LOW and *EXPOSE* goes HIGH. *cnt* is set to 29 and begins decrementing for each clock cycle. The *exposure* state is stopped short at cycle 22, where *rst* goes high for one cycle. As desired, this returns the camera to the *idle* state and sets *exp\_time* back to its default, 16.

Then, from cycle 24 to 39, exp\_decrease is set LOW. exp\_time decrements as intended, and stays constant after it reaches the minimum of 2. In the 40th cycle, init is HIGH again, causing the camera to enter the exposure state. cnt is set to 1, and decrements for one cycle, after which it has reached 0. True to the FSM illustrated in figure 5, this prompts the camera to enter the readout state.

The *cnt* register is set to 8 as the camera switches to *readout*. It rightfully decrements for each clock cycle, and the output signals act exactly as specified for the *readout* state in figure 6. When the readout is finished, i.e. after *cnt* has reached 0, the camera enters the *idle* state again.

# 4 Discussion

#### 4.1 Process variation

The values for  $R_{DS}$  for a switch transistor turned off is  $5G\Omega$  in FF,  $500G\Omega$  in TT and  $50T\Omega$ . For a voltage of 1V this means a leakage of 200pA in FF, and that is actually quite dramatic in our circuit. In SS however, a voltage of 1V means a leakage current of 20fA, and that is actually better for our circuit than the TT case.

The  $R_{DS}$  values when the transistors are switched on, however are not varying that much. The  $R_{DS}$  values for FF, TT and SS respectively are  $500\mathrm{k}\Omega$ ,  $750\mathrm{k}\Omega$  and  $1\mathrm{M}\Omega$ . To conduct a current of 1nA, the required voltages are respectively  $500\mu\mathrm{V}$ ,  $750\mu\mathrm{V}$  and 1mV. All these values are very small compared to  $V_{DD}$ , so when switched on, our transistors can be considered ideal conductors for practical purposes.

For the full analog circuit, we can see as expected that the way in which the FF corner increases leakage current has a dramatic impact on the system as a whole, while the way SS increases the on resistance does not make a big change. And the cool thing is that SS also reduces leakage current compared to TT, so that SS in total improves behaviour of our design.

# 4.2 Modular digital design

In this project's digital circuit, only one module is used, which is illutrated in figure 7 and implemented in Verilog in appendix C. This choice may be controversial, as many prefer a

more modular design. However, having several modules for this project seemed excessive and unnecessarily complex. This is a very simple, low-resolution, black-and-white camera, and the single-module implementation is not particularly challenging to read or understand. Modulisation was therefore opted out in this project. However, in a natural continuation of the project, like increasing the resolution or enabling colour, dividing the digital design into modules is very much relevant.

# Appendices

# A Analog simulation graphs

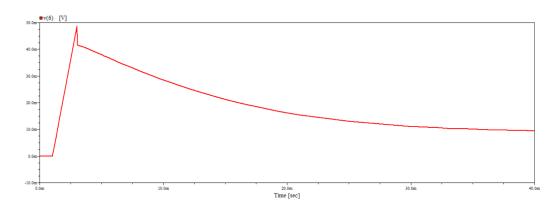


Figure 9: Minimum exposure time - minimum light

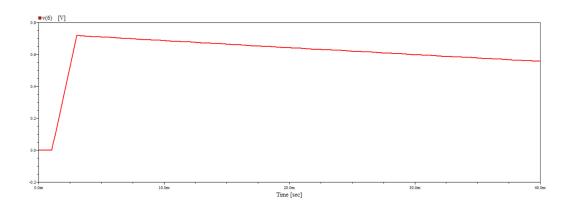


Figure 10: Minimum exposure time - maximum light

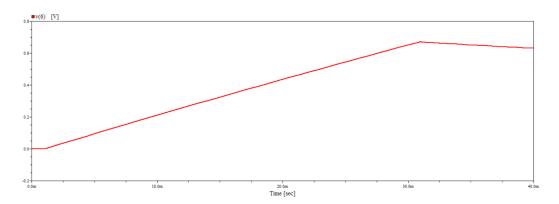


Figure 11: Maximum exposure time - minimum light

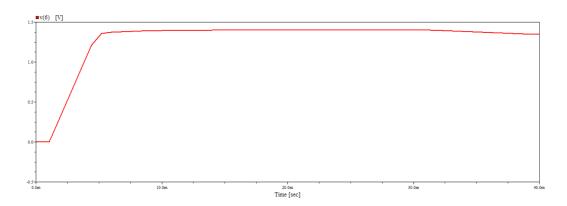


Figure 12: Maximum exposure time - maximum light

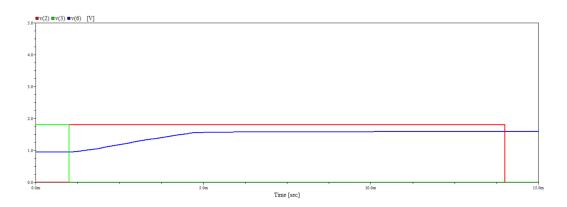


Figure 13: Simulation for maximizing dynamic range of M3 and active load.

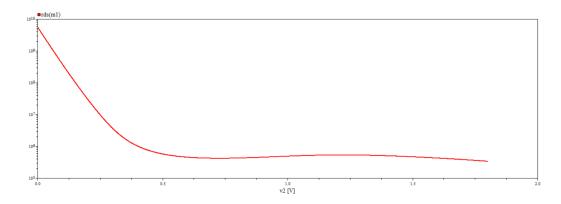


Figure 14: FF corner simulation of  $R_{DS}$  of NMOS switch as function of  $V_{GS}$ .  $V_{DS}=1.8\mathrm{V}$ .

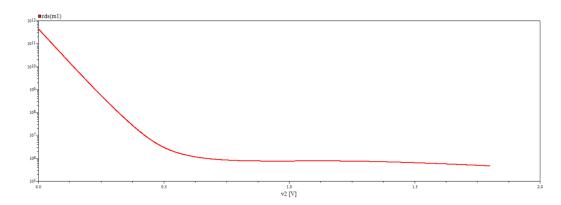


Figure 15: TT corner simulation of  $R_{DS}$  of NMOS switch as function of  $V_{GS}$ .  $V_{DS}=1.8\mathrm{V}$ .

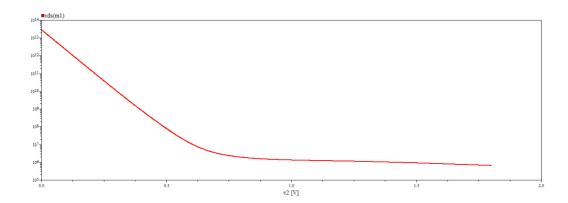


Figure 16: SS corner simulation of  $R_{DS}$  of NMOS switch as function of  $V_{GS}$ .  $V_{DS}=1.8\mathrm{V}$ .

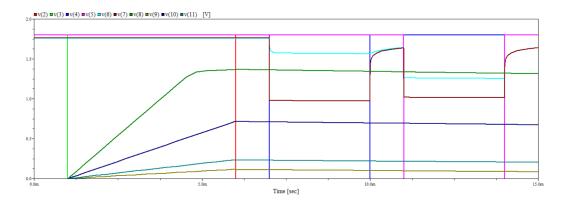


Figure 17: Simulation of analog circuit. The color(node nr)'s are: red(2): EXPOSE, light green(3): ERASE, blue(4): NRE\_1, magenta(5): NRE\_2, light blue(6): OUT1, brown(7): OUT2, dark green(8):  $V_{C11}$ , mustard(9):  $V_{C12}$ , dark blue(10):  $V_{C21}$ , teal(11):  $V_{C22}$ .

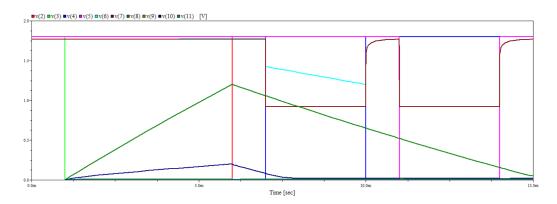


Figure 18: FF corner simulation of full analog circuit. Colors are the same as in figure 17.

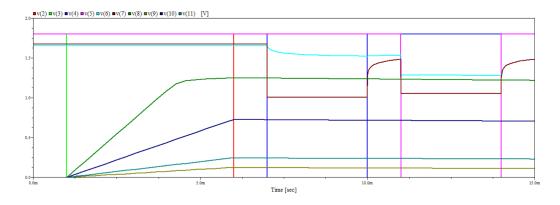


Figure 19: SS corner simulation of full analog circuit. Colors are the same as in figure 17.

B Spice code

# C Verilog code